

V <sub>DSS</sub>	600V
R <sub>DS(on)</sub> (Max.)	0.234Ω
I <sub>D</sub>	±20A
P <sub>D</sub>	76W

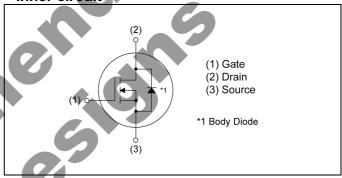
## Outline



### Features

- 1) Fast reverse recovery time (trr)
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Drive circuits can be simple
- 5) Pb-free plating; RoHS compliant

# ●Inner circuit



# Application

Switching applications

Packaging specifications

Packing	Tube
Packing code	C8
Marking	R6020JNZ
Basic ordering unit (pcs)	360

## ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V <sub>DSS</sub>	600	V
Continuous drain current (T <sub>c</sub> = 25°C)	I <sub>D</sub> *1	±20	А
Pulsed drain current	I <sub>DP</sub> *2	±60	А
Gate - Source voltage	$V_{GSS}$	±30	V
Avalanche current, single pulse	l <sub>AS</sub> *3	4.8	А
Avalanche energy, single pulse	E <sub>AS</sub> *3	618	mJ
Power dissipation (T <sub>c</sub> = 25°C)	P <sub>D</sub>	76	W
Junction temperature	Tj	150	°C
Operating junction and storage temperature range	T <sub>stg</sub>	-55 to +150	°C

### ●Thermal resistance

Davamatav	Cymah al	Values			1.1:4
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	R <sub>thJC</sub>	-	-	1.64	°C/W
Thermal resistance, junction - ambient	R <sub>thJA</sub>	-	-	40	°C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>	-	4	265	°C

## ● Electrical characteristics (T<sub>a</sub> = 25°C)

- Ziesti isai siiai astoristiss (+a						
Parameter	Symbol	Conditions	Values			Unit
	- Cymicon	Containe	Min.	Тур.	Max.	
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V, I_D = 1mA$	600	-	1	V
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 600V, V_{GS} = 0V$ $T_j = 25^{\circ}C$	-	ı	100	μA
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30V, V_{DS} = 600V$	-	-	±100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 3.5 \text{mA}$	5.0	6.0	7.0	V
Static drain - source on - state resistance	R <sub>DS(on)</sub> *5	$V_{GS} = 15V, I_D = 10A$ $T_j = 25^{\circ}C$	-	0.180	0.234	Ω
Gate resistance	R <sub>G</sub>	f = 1MHz, open drain	-	2.0	-	Ω



# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Davamatav	Cymah al	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Uniil
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	1500	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 100V	-	90	-	
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	1.9		_
Effective output capacitance energy related	C <sub>o(er)</sub> *6	V <sub>GS</sub> = 0V	-	68	5	pF
Effective output capacitance time related	C <sub>o(tr)</sub> *7	V <sub>DS</sub> = 0V to 480V	-	270	-	
Turn - on delay time	t <sub>d(on)</sub> *5	$V_{DD} \simeq 300V$ , $V_{GS} = 15V$		29	-	
Rise time	<b>t</b> <sub>r</sub> *5	I <sub>D</sub> = 3.5A	-	22	-	20
Turn - off delay time	t <sub>d(off)</sub> *5	R <sub>L</sub> ≃ 30.1Ω	-	56	-	ns
Fall time	<b>t</b> <sub>f</sub> *5	$R_G = 10\Omega$	-	11	-	

# ● Gate charge characteristics (T<sub>a</sub> = 25°C)

Doromotor	Symbol Conditions		Values			l loit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Total gate charge	$Q_g^{*5}$	V <sub>DD</sub> ≈ 300V	-	45	-	
Gate - Source charge	Q <sub>gs</sub> *5	I <sub>D</sub> = 20A	-	15	-	nC
Gate - Drain charge	Q <sub>gd</sub> *5	V <sub>GS</sub> = 15V	-	17	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} \simeq 300V$ , $I_D = 20A$	-	9.5	-	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*2</sup> Pw ≤ 10µs, Duty cycle ≤ 1%

<sup>\*3</sup> L  $\simeq$  50mH,  $V_{DD}$  = 50V,  $R_G$  = 25 $\Omega$ , starting  $T_i$  = 25°C

<sup>\*4</sup> Tc=25°C

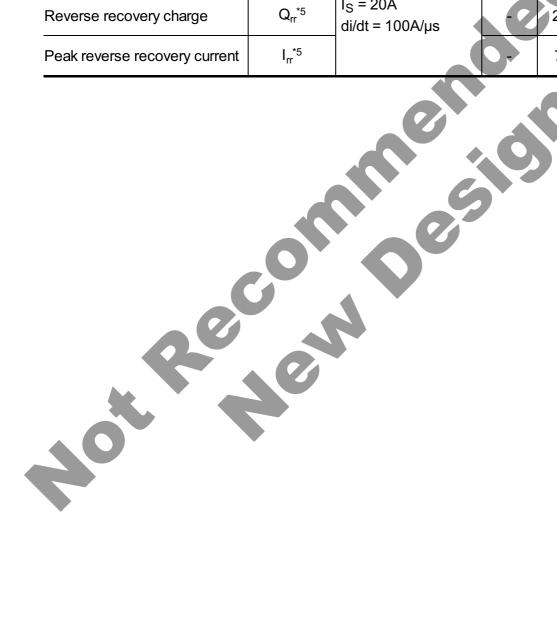
<sup>\*5</sup> Pulsed

<sup>\*6</sup> Co(er) is a fixed capacitance that gives the same stored energy as Coss while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>\*7</sup> Co(tr) is a fixed capacitance that gives the same charging time as Coss while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Cumbal	Conditions	Values			Unit	
Parameter	Symbol Conditions		Min.	Тур.	Max.	Offic	
Source current	I <sub>S</sub> *1	- T <sub>C</sub> = 25°C	1	1	20	A	
Pulsed source current	I <sub>SP</sub> *2	1C - 23 C	1	-	60	А	
Source-Drain voltage	V <sub>SD</sub> *5	$V_{GS} = 0V, I_{S} = 20A$	-	-	1.7	V	
Reverse recovery time	<b>t</b> <sub>rr</sub> *5		-	85	-	ns	
Reverse recovery charge	Q <sub>rr</sub> *5	I <sub>S</sub> = 20A di/dt = 100A/μs	?	280	-	nC	
Peak reverse recovery current	<sub>rr</sub> *5		<b>•</b>	7.5	-	Α	



### • Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

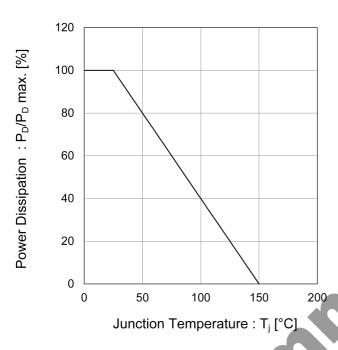


Fig.2 Drain Current Derating
Curve vs. Ambient Temperature

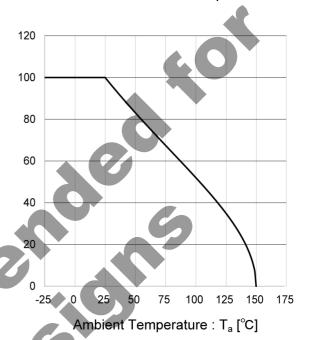


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

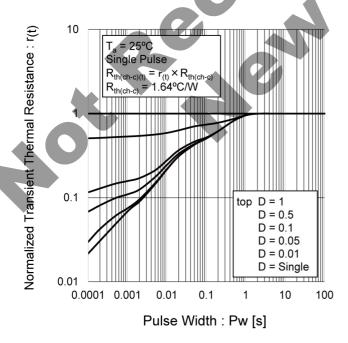
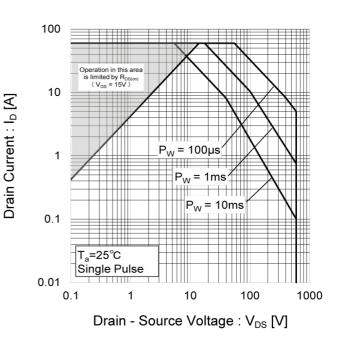


Fig.4 Maximum Safe Operating Area



rain Current Dissipation: I<sub>D</sub>/I<sub>D</sub>max. [%]

### Electrical characteristic curves

Fig.5 Avalanche Energy Derating
Curve vs. Junction Temperature

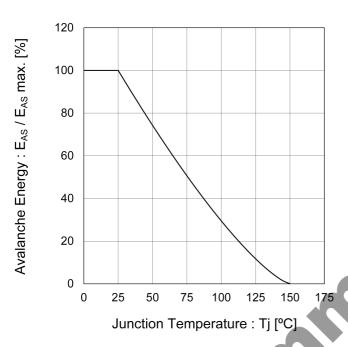


Fig.6 Normalized Breakdown Voltage vs. Junction Temperature

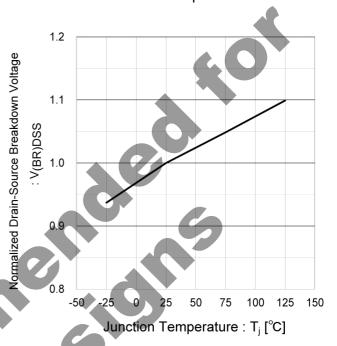


Fig.7 Typical Output Characteristics(I)

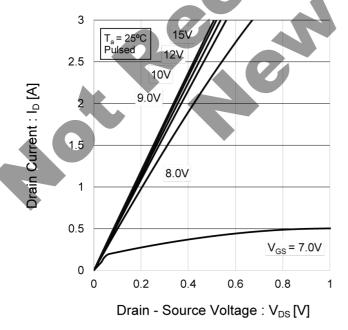
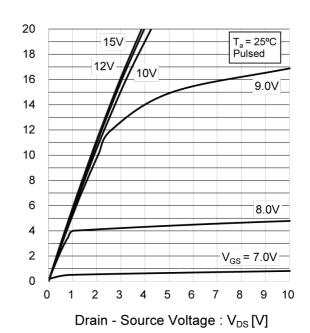


Fig.8 Typical Output Characteristics(II)



Drain Current : I<sub>D</sub> [A]

### Electrical characteristic curves

Fig.9 Typical Transfer Characteristics

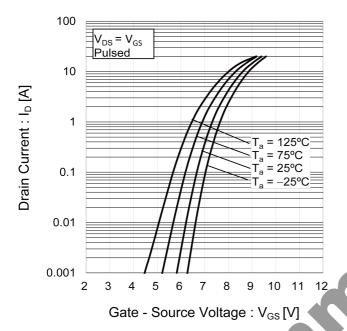


Fig.10 Normalized Gate Threshold .

Voltage vs Junction Temperature

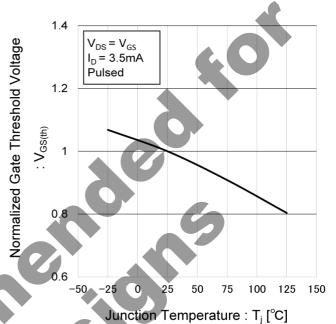
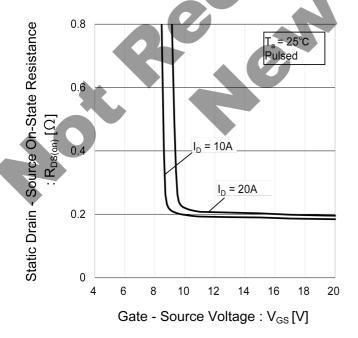
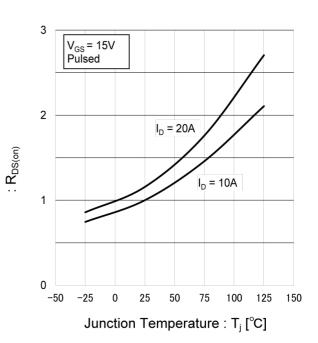


Fig.11 Static Drain - Source On - State
Resistance vs. Gate Source Voltage



rig.12 Normalized Static Drain - Source On - State Resistance vs. Junction Temperature



Normalized Static Drain - Source On-State Resistance

### • Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

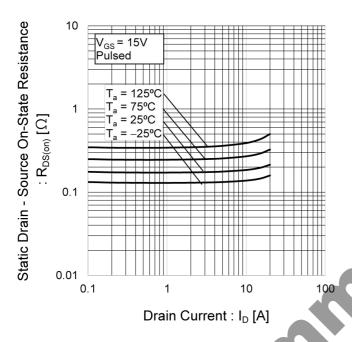


Fig.14 Typical Capacitance vs.
Drain - Source Voltage

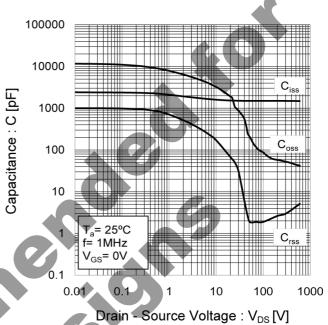


Fig.15 Typical Coss Stored Energy

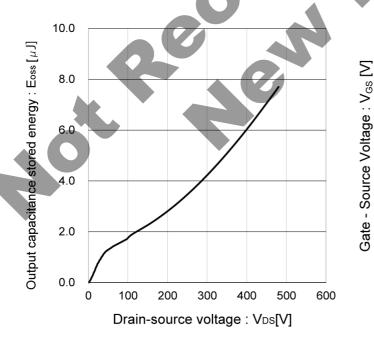
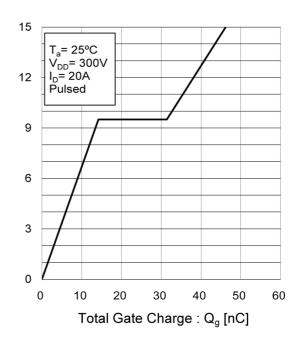
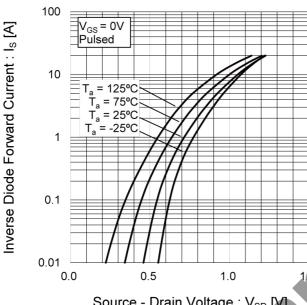


Fig.16 Dynamic Input Characteristics



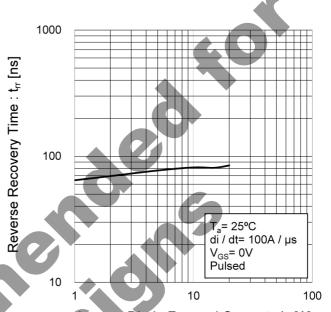
### • Electrical characteristic curves

Fig.17 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V<sub>SD</sub> [V]

Fig.18 Reverse Recovery Time vs. Inverse Diode Forward Current



Inverse Diode Forward Current: Is [A]



### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

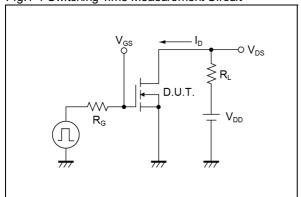


Fig.2-1 Gate Charge Measurement Circuit

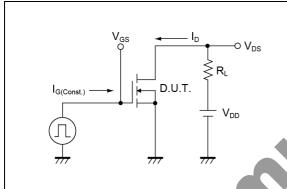


Fig.3-1 Avalanche Measurement Circuit

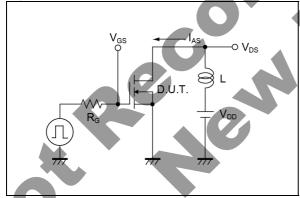


Fig.4-1 Diode Recovery Measurement Circuit

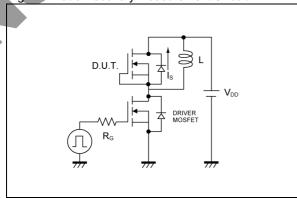


Fig.1-2 Switching Waveforms

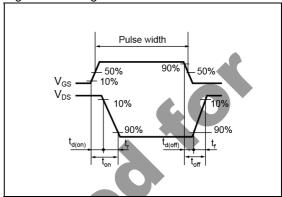


Fig.2-2 Gate Charge Waveform

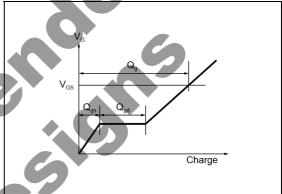


Fig.3-2 Avalanche Waveform

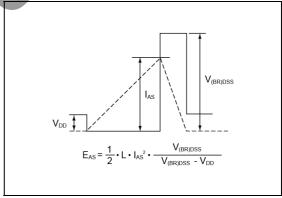
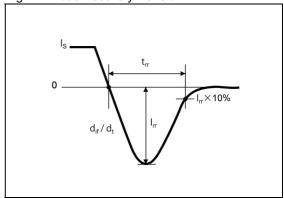
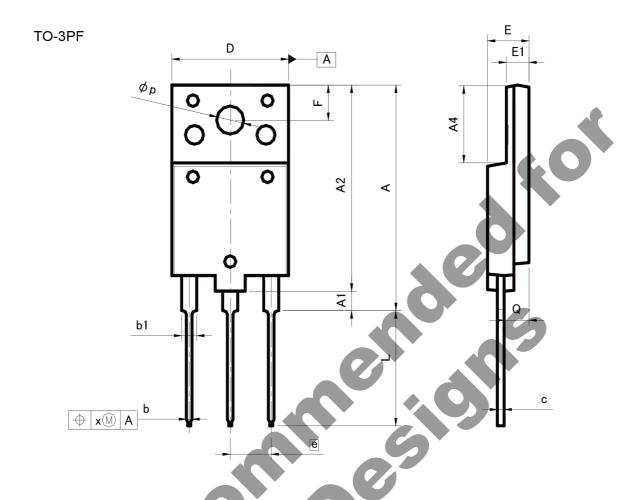


Fig.4-2 Diode Recovery Waveform



### Dimensions



DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	26.30	26.70	1.035	1.051
A1	2.30	2.70	0.091	0.106
A2	26.30	26.70	1.035	1.051
A4	9.80	10.20	0.386	0.402
b	0.65	0.95	0.026	0.037
b1	1.80	2.20	0.071	0.087
С	0.80	1.10	0.031	0.043
D	15.30	15.70	0.602	0.618
Е	5.30	5.70	0.209	0.224
е	5.4	45	0.215	ı
E1	2.80	3.20	0.110	0.126
F	4.30	4.70	0.169	0.185
L	14.60	15.00	0.575	0.591
р	3.40	3.80	0.134	0.150
Q	3.10	3.50	0.122	0.138
Х	_	0.50	_	0.020

Dimension in mm/inches

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  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
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- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

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  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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